

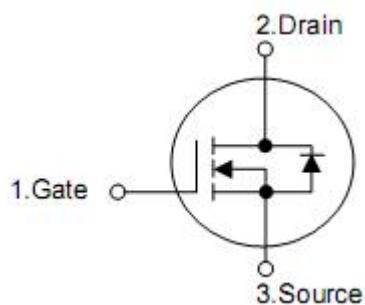
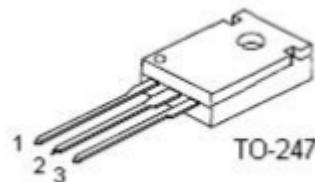
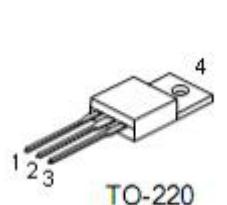
1. Applications

- Power supply
- DC-DC converters

2. Features

- $R_{DS(on)} = 7m\Omega(\text{typ.}) @ V_{GS} = 10 \text{ V}$
- Lead free and Green device available
- Low RDS-on to minimize conductive loss
- High avalanche current

3. Pin configuration



Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

4. Ordering Information

Part Number	Package	Brand
KNP3306A	TO-220	KIA
KNM3306A	TO-247	KIA

5. Absolute maximum ratings

(T _C = 25°C , unless otherwise specified)				
Parameter	Symbol	Rating		Units
		TO-220	TO-247	
Drain-source voltage	V _{DSS}	60		V
Gate-source voltage	V _{GSS}	±25		V
Continuous Drain Current	I _D ³	80		A
		60		
Pulsed Drain Current	I _{DP} ⁴	300		
Avalanche Current	I _{AS} ⁵	21.5		
Avalanche Energy	E _{AS} ⁵	462.25		mJ
Maximum Power Dissipation	P _D	183	215	W
		92	107.5	
Junction & Storage Temperature Range	T _L , T _{STG}	-55~+175		°C

6. Thermal characteristics

Symbol	Parameter	Typical		Unit
		TO-220	TO-247	
R _{θJC}	Thermal Resistance, Junction-to-Case	0.68	0.58	°C /W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5		

7. Electrical characteristics

($T_J=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	60	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=48\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
		$T_J=125^\circ\text{C}$	-	-	100	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}}=+25\text{V}, V_{\text{DS}}=0\text{V}$	-	-	+100	nA
		$V_{\text{GS}}=-25\text{V}, V_{\text{DS}}=0\text{V}$	-	-	-100	nA
On characteristics						
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	2.0	3.0	4.0	V
Drain-source on resistance	$R_{\text{DS}(\text{on})}$ ¹	$V_{\text{GS}}=10\text{V}, I_D=30\text{A}$	-	7	8.5	$\text{m}\Omega$
Dynamic Characteristics²						
Input capacitance	C_{iss}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	3390	-	pF
Output capacitance	C_{oss}		-	371	-	
Reverse transfer capacitance	C_{rss}		-	258	-	
Gate Repacitance	R_G	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, F=1.0\text{MHz}$	-	1.8	-	Ω
Total gate charge	Q_g	$V_{\text{DS}}=30\text{V}, I_D=30\text{A}, V_{\text{GS}}=10\text{V},$	-	73	-	nC
Gate-source charge	Q_{gs}		-	18	-	
Gate-drain charge	Q_{gd}		-	22	-	
Resistive swiching characteristics²						
Turn-on delay time	$t_{\text{d}(\text{ON})}$	$V_{\text{DD}}=30\text{V}, I_D=30\text{A}, V_{\text{GS}}=10\text{V}$ $R_G=6.8\Omega$	-	18	-	ns
Rise time	t_{rise}		-	120	-	
Turn-off delay time	$t_{\text{d}(\text{OFF})}$		-	55	-	
Fall time	t_{fall}		-	68	-	
Diode Characteristics						
Diode Forward Voltage	V_{SD} ¹	$V_{\text{GS}}=0\text{V}, I_{\text{SD}}=20\text{A}$	-	-	1.3	V
Diode Continuous Forwardcurrent	I_S ³		-	-	114	A
Reverse recovery time	t_{rr}	$I_F=30\text{A}, \text{di}/\text{dt}=100\text{A}/\mu\text{s}$	-	45	-	ns
Reverse recovery charge	Q_{rr}		-	76	-	nC

Note:

- 1: Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- 2: Guaranteed by design, not subject to production testing.
- 3: Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 55A.
- 4: Repetitive rating, pulse width limited by max junction temperature.
- 5: Starting $T_J=25^\circ\text{C}$, $V_D=50\text{V}$, $L=0.5\text{mH}$, $I_{AS}=43\text{A}$.

8. Typical Characteristics

